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	Document ID	Kind Codes	Source	Issue Date	Pages	Title	Abstract	Current OR	Retrieval Classif	Current XRef	Inventor	U	S	C	P	1	2	3	4	5
1	US 4583122 A		USPAT	19860415	11	Imaging display device	An imaging display device characterized by comprising a pair of transparent substrates which are arranged in opposition to each other with a predetermined interval therebetween, photoelectric elements which are disposed in a large number between the substrates and in adjacency to one of the substrates and which convert light signals from outside the one substrate into electric signals, and a large number of electrooptic elements which are disposed between the other substrate and the respective photoelectric elements and in a predetermined relationship of	348/792		396/373	Ohwada, Junichi, et al.	☐	☒	☐	☐	☐	☐	☐	☐	☐
2	US 4686554 A		USPAT	19870811	80	Photoelectric converter	A photoelectric converter comprising a photosensor element, a typical example of the photosensor element comprising: a transistor including an n or n.sup.+ collector region an n.sup.- region disposed contiguous to the collector region, a p base region disposed contiguous to the n.sup.- region, an n.sup.+ emitter region disposed contiguous to the base region, and a first electrode connected to the emitter region; and a storage capacitor constituted by the base region, an electrically insulating region disposed contiguous to the base region, and a second	257/443		257/291 ; 348/294	Ohmi, Tadahiro, et al.	☐	☒	☐	☐	☐	☐	☐	☐	☐

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3	US 4791469 A		USPAT	19881213	79	Photoelectric converter	A photoelectric converter comprising a photosensor element, a typical example of the photosensor element comprising: a transistor including an n or n.sup.+ collector region an n.sup.- region disposed contiguous to the collector region, a p base region disposed contiguous to the n.sup.- region, an n.sup.+ emitter region disposed contiguous to the base region, and a first electrode connected to the emitter region; and a storage capacitor constituted by the base region, an electrically insulating region disposed contiguous to the base region and a second	257/462		257/465 ; 257/513 ; 327/515	Ohmi, Tadahiro , et al.	☐	☒	☐	☐	☐	☐	☐	☐	☐
4	US 4916512 A		USPAT	19900410	82	Photoelectric converter	A photoelectric converter comprising a photosensor element, a typical example of the photosensor element comprising: a transistor including an n or n.sup.+ collector region an n.sup.- region disposed contiguous to the collector region, a p base region disposed contiguous to the n.sup.- region, an n.sup.+ emitter region disposed contiguous to the base region, and a first electrode connected to the emitter region; and a storage capacitor constituted by the base region, an electrically insulating region disposed contiguous to the base region and a second	348/314		257/290 ; 257/443 ; 257/462	Ohmi, Tadahiro , et al.	☐	☒	☐	☐	☐	☐	☐	☐	☐

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5	US 4942474 A		USPAT	19900717	23	Solid-state imaging device having photo-electric conversion elements and other circuit elements arranged to provide improved photo-sensitivity	A solid-state imaging device including a plurality of photoelectric conversion elements (for example, photodiodes) arranged on a semiconductor substrate so as to form a matrix and read-out means for reading out signal charges which are stored in the photodiodes in accordance with incident light, in a predetermined order, is disclosed in which device the read-out means is made up of a plurality of active elements such as a MOS transistor connected to a photodiode, part of the active elements are used as a pixel amplifier for amplifying the signal charge of the	348/301		348/241 ; 348/310	Akimoto, Hajime , et al.	☐	☒	☐	☐	☐	☐	☐	☐	☐
6	US 4954895 A		USPAT	19900904	17	Solid-state imaging device including photoelectric conversion elements integrated at a surface of a semiconductor substrate	A solid-state imaging device has a plurality of photodiodes (photoelectric conversion elements) formed in a surface of a semiconductor substrate in a matrix configuration and reading means for reading out signal charges stored in the photodiodes in accordance with the incident lights in a predetermined order. This reading means includes active elements, such as MOS type transistors, connected to each of the photodiodes. A MOS type transistor constituting part of theses active elements is provided in the path of the transmitting incident light for the associated	348/301		257/292 ; 348/273 ; 348/310	Akimoto, Hajime , et al.	☐	☒	☐	☐	☐	☐	☐	☐	☐

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7	US 5016108 A		USPAT	19910514	15	Solid-state imaging device having series-connected pairs of switching MOS transistors for transferring signal electric charges therethrough	A solid-state imaging device has a plurality of light receiving elements formed in a semiconductor substrate. Signal electric charges generated by light incident upon the light receiving elements and stored in the individual light receiving elements are sequentially read out through signal lines by scanning a plurality of switches. Each of the switches includes a series connection of a first MOS transistor switching element formed in the semiconductor substrate and a second MOS transistor formed in a semiconductor provided above the semiconductor substrate	348/302		348/299	Akimoto, Hajime, et al.	☐	☒	☐	☐	☐	☐	☐	☐	☐
8	US 5128735 A		USPAT	19920707	67	Photoelectric converter with phototransistor and refresh means	A photoelectric converter comprising a photosensor element, a typical example of the photosensor element comprising: a transistor including an n or n.sup.+ collector region an n.sup.- region disposed contiguous to the collector region, a p base region disposed contiguous to the n.sup.- region an n.sup.+ emitter region disposed contiguous to the base region, and a first electrode connected to the emitter region; and a storage capacitor constituted by the base region, an electrically insulating region disposed contiguous to the base region, and a second	257/462		250/208.1; 257/443	Ohmi, Tadahiro, et al.	☐	☒	☐	☐	☐	☐	☐	☐	☐

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9	US 5132811 A		USPAT	19920721	32	Holographic operating optical apparatus	A holographic apparatus has an inferometer for concurrently irradiating an image recording medium by a writing reference light of spherical or plane wave form and a signal light containing image information which interfere. with each other to form a hologram, and means for irradiating the hologram by a reading reference light in the opposite direction of the reference light to thereby reconstruct the image information. The image recording medium is comprised of a photoconductive layer, an optical reflective layer, a pair of liquid crystal alignment layers a	359/6		348/40 ; 349/1 ; 349/17 ; 349/172 ; 349/25 ; 349/27 ; 359/561 ; 359/7 ; 706/40	Iwaki, Tadao , et al.	☐	☒	☐	☐	☐	☐	☐	☐	☐
10	US 5146299 A		USPAT	19920908	36	Ferroelectric thin film material, method of deposition, and devices using same	A ferroelectric device that comprises a polarizing thin film of BaMF.sub.4 deposited on a substrate. Ba is barium, M is one of the metals of the group consisting of iron (FE), manganese (Mn), cobolt (Co), nickel (Ni), magnesium (Mg), and zinc (Zn). The substrate is silicon, sapphire, or gallium arsenide. A non-volatile NDRO and DRO memory cell and methods for depositing the thin film. A	257/295		257/314 ; 361/321.1 ; 365/145 ; 365/156 ; 365/176	Lampe, Donald R. , et al.	☐	☒	☐	☐	☐	☐	☐	☐	☐

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11	US 5179428 A		USPAT	19930112	21	Three dimensional CCD image sensor	A three-dimensional CCD image sensor comprising a plurality of N type light receiving regions being formed on a two-dimensional plane; a plurality of N type VCCD regions being formed under said plurality of N type light receiving regions; a series of arrangement that said plurality of N type light receiving regions and said plurality of N type VCCD regions are formed opposite to each other being configured in sequence at a desired interval; a desired area of a charge transfer path being formed between each of said plurality of N type light receiving regions and	257/233		257/292 ; 348/315	Lee, Sung M.	☐	☒	☐	☐	☐	☐	☐	☐	☐
12	US 5210434 A		USPAT	19930511	76	Photoelectric converter with scanning circuit	A photoelectric converter comprising a photosensor element, a typical example of the photosensor element comprising: a transistor including an n or n.sup.+ collector region an n.sup.- region disposed contiguous to the collector region, a p base region disposed contiguous to the n.sup.- region, an n.sup.+ emitter region disposed contiguous to the base region, and a first electrode connected to the emitter region; and a storage capacitor constituted by the base region, an electrically insulating region disposed contiguous to the base region, and a second	257/291		250/208.1 ; 257/292 ; 257/443 ; 257/446 ; 327/515	Ohmi, Tadahiro, et al.	☐	☒	☐	☐	☐	☐	☐	☐	☐

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13	US 5386720 A		USPAT	19950207	39	Integrated AFM sensor	An integrated AFM sensor includes a cantilever which has two beams extending from a support portion. The beams are integrated with each other at their ends to form a triangular free end, and a probe having a sharp distal end is arranged at the free end. The cantilever is formed by stacking a passivation layer, a piezoresistive layer, and a silicon layer. Electrodes electrically connected to the piezoresistive layer are formed	73/105		250/306 ; 250/307	Toda, Akitoshi , et al.	☐	☒	☐	☐	☐	☐	☐	☐	☐
14	US 5440141 A		USPAT	19950808	26	Method of measuring a thickness of a multilayered sample using ultraviolet light and light with wavelengths longer than ultraviolet	Spectral reflection ratios with respect to a second wavelength range are obtained and Fourier transformed to derive frequency converted spectrum. A power spectrum is obtained from the frequency converted spectrum to identify a peak which expresses interference caused by a silicon film. An approximate value d2' of the film thickness of the silicon film is calculated based on the peak position. After filtered by low-pass filtering, the frequency converted spectrum is reverse Fourier transformed to obtain spectral reflectance. From the spectral	250/559 .27		250/226 ; 356/357	Horie, Masahiro	☐	☒	☐	☐	☐	☐	☐	☐	☐

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15	US 5464984 A		USPAT	19951107	29	X-ray imaging system and solid state detector therefor	An x-ray detector includes a scintillator, a sensor array, processing circuits, and a ceramic layer. The ceramic layer overlays the processing circuits. The pixel architecture of the detector utilizes a technique similar to a CCD array to shift data from the array. The detector preferably utilizes 4-side abuttable sensor arrays having imbedded shift registers and bond pads superimposed over the pixel array in the upper metallization layers of the sensor. An alternative embodiment incorporates a silicon-on-insulator substrate to produce a monolithic	250/370.11		250/366; 250/370.09	Cox, John D., et al.	☐	☒	☐	☐	☐	☐	☐	☐	☐
16	US 5497246 A		USPAT	19960305	42	Image signal processing device	A DCT processing circuit outputs DCT coefficients based on image data stored in an image memory. The DCT coefficients are quantized by a quantization processing circuit, then input to a Huffman encoding processing circuit and an inverse quantization processing circuit. In the inverse quantization processing circuit, the DCT coefficients are reproduced. The differences between the reproduced DCT coefficients and the DCT coefficients output from the DCT processing circuit are determined as the quantized error data by subtractors. An error data synthesizing	358/426		348/403; 348/404; 348/405; 358/430; 358/432; 382/248; 382/250; 382/251; 382/252	Abe, Nobuaki	☐	☒	☐	☐	☐	☐	☐	☐	☐

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17	US 5563431 A		USPAT	19961008	70	Photoelectrical converter with refresh means	A photoelectric converter is adapted for an accumulation operation, readout operation and refresh operation. The photoelectric converter includes a transistor including a control electrode region having a semiconductor of a first conductivity type, a first main electrode region comprising a semiconductor of a second conductivity type different from the first conductivity type and disposed electrically connectable to an output circuit including a capacitive load, and a second main electrode region of the second conductivity type, the control electrode region being	257/291		250/208.1 ; 257/292 ; 257/443 ; 257/446 ; 257/448 ; 307/117	Ohmi, Tadahiro, et al.	☐	☒	☐	☐	☐	☐	☐	☐	☐
18	US 5582640 A		USPAT	19961210	154	Semiconductor device and its fabricating method	A single crystal and a polycrystal having an excellent crystal quality and providing a highly reliable semiconductor device are formed by solid phase growth at low temperatures. An amorphous thin film is deposited on a substrate such that an average inter-atomic distance of main constituent element of the amorphous thin film is 1.02 times or more of an average inter-atomic distance of the elements in single crystal, and crystallization energy is applied to the amorphous thin film to perform solid phase growth to thereby form a single crystal. In another embodiment	117/8		117/930 ; 438/166 ; 438/481 ; 438/486	Okada, Takako, et al.	☐	☒	☐	☐	☐	☐	☐	☐	☐

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19	US 5604364 A		USPAT	19970218	69	Photoelectric converter with vertical output lines	A photoelectric converter comprising a photosensor element, a typical example of the photosensor element comprising: a transistor including an n or n.sup.+ collector region an n.sup.- region disposed contiguous to the collector region, a p base region disposed contiguous to the n.sup.- region, an n.sup.+ emitter region disposed contiguous to the base region, and a first electrode connected to the emitter region; and a storage capacitor constituted by the base region, an electrically insulating region disposed contiguous to the base region and a second	257/291		250/208.1 ; 257/292 ; 257/443 ; 257/448 ; 307/117	Ohmi, Tadahiro , et al.	☐	☒	☐	☐	☐	☐	☐	☐	☐
20	US 5642129 A		USPAT	19970624	18	Color sequential display panels	A color active matrix display system allows random access of pixel electrodes. The control electronics is fabricated with the active matrix circuitry using single crystal silicon technology. The control electronics includes a random access data scanner and random access spec scanners. By selectively actuating pixel electrodes in the active matrix display region, compressed video information can be directly displayed on the active matrix display panel. Color stripes are used to generate sequential color systems to produce a	345/100		345/88 ; 345/92 ; 345/98	Zavracky , Matthew , et al.	☐	☒	☐	☐	☐	☐	☐	☐	☐

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21	US 5666209 A		USPAT	19970909	20	Image signal processing device	An image signal processing device generates first image data and second image data based on the same optical image. Each pixel of the second image data is offset from the corresponding pixel of the first image data by half the distance between the centers of two adjacent pixels. The first image data is then subjected to a discrete cosine transformation (DCT), quantization, and Huffman encoding, and is recorded to an IC memory card. High resolution image data is generated based on the first and second image data. Expanded image data is obtained based on the first	386/109		348/397 ; 348/405 ; 348/412 ; 386/112	Abe, Nobuaki	☐	☒	☐	☐	☐	☐	☐	☐	☐
22	US 5673059 A		USPAT	19970930	44	Head-mounted display apparatus with color sequential illumination	A color active matrix display system allows random access of pixel electrodes. The control electronics is fabricated with the active matrix circuitry using single crystal silicon technology. The control electronics includes a random access data scanner and random access spec scanners. By selectively actuating pixel electrodes in the active matrix display region, compressed video information can be directly displayed on the active matrix display panel. Color stripes are used to generate sequential color systems to produce a	345/8		348/53	Zavracky, Matthew, et al.	☐	☒	☐	☐	☐	☐	☐	☐	☐

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23	US 5689612 A		USPAT	19971118	19	Image signal processing device	An image signal processing device generates first image data and second image data based on the same optical image. Each pixel of the second image data is offset from the corresponding pixel of the first image data by half the distance between the centers of two adjacent pixels. The first image data is then subjected to a discrete cosine transformation (DCT), quantization, and Huffman encoding, and is recorded to an IC memory card. High resolution image data is generated based on the first and second image data. Expanded image data is obtained based on the first	386/109		348/397 ; 348/405 ; 348/409 ; 348/412 ; 386/112 ; 386/124	Abe, Nobuaki	☐	☒	☐	☐	☐	☐	☐	☐	☐
24	US 5714752 A		USPAT	19980203	21	Image pickup device in which the light receiving element, the drive circuit for illuminating means, and the drive circuit for the light receiving element are on the same chip	An image pickup device comprises illuminating means for illuminating an object and an image pickup element for picking up an image of the object. An improvement is in that a drive circuit for driving the illuminating means and a control circuit for controlling the driving of the image pickup device are integrated with the image pickup device into one chip,	250/208.1		250/214.1 ; 358/475 ; 358/482	Ueno, Isamu, et al.	☐	☒	☐	☐	☐	☐	☐	☐	☐

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25	US 5751261 A		USPAT	19980512	26	Control system for display panels	A control apparatus for an active matrix liquid crystal display device is fabricated with the active matrix as a single integrated SOI circuit. The control apparatus and the active matrix are lifted from a silicon substrate and transferred to a glass substrate as a single piece. The control apparatus comprises a video interface, a column driver, and dual row drivers. The video interface operates the active matrix as a multiple-frequency scanning display device. The polarities of the display pixels are reversed on every frame by a polarity switch coupled	345/55		345/99	Zavracky, Matthew, et al.	☐	☒	☐	☐	☐	☐	☐	☐	☐
26	US 5781164 A		USPAT	19980714	21	Matrix display systems	A passive matrix display device obtains fast response times and high resolutions by fabricating the control circuitry and passive matrix electrodes together as a single monolithic device. The electrodes and the control circuitry are fabricated as an SOI structure on a substrate. The structure is removed from the substrate and transferred to a glass substrate using a lift-off and transfer process. Performance is further	345/87		345/206; 349/140	Jacobsen, Jeffrey, et al.	☐	☒	☐	☐	☐	☐	☐	☐	☐

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27	US 5806072 A		USPAT	19980908	138	Electronic imaging apparatus having hierarchical image data storage structure for computer-compatible image data management	An image incident on an image sensor is photoelectrically converted to digital image data and stored on a storage device or medium in a hierarchical form as a file in a directory or subdirectory supported by a disk operating system. In this way, the system realizes an electronic	707/200		348/231 ; 348/232 ; 707/100 ; 707/104	Kuba, Hirokazu, et al.	☐	☒	☐	☐	☐	☐	☐	☐	☐
28	US 5814866 A		USPAT	19980929	26	Semiconductor device having at least one field oxide area and CMOS vertically modulated wells (VMW) with a buried implanted layer for lateral isolation having a first portion below a well, a second portion forming another, adjacent well, and a vertical po	CMOS vertically modulated wells have a structure with a buried implanted layer for lateral isolation (BILLI). This structure includes a field oxide area, a first retrograde well of a first conductivity type, a second retrograde well of a second conductivity type adjacent the first well, and a BILLI layer below the first well and connected to the second well by a vertical portion. This structure has a distribution in depth underneath the field oxide which kills	257/369		257/350 ; 257/351 ; 257/371 ; 257/372 ; 438/228 ; 438/526 ; 438/529	Borland, John O.	☐	☒	☐	☐	☐	☐	☐	☐	☐

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29	US 5847422 A		USPAT	19981208	12	MOS-based active pixel sensor cell that utilizes the parasitic bipolar action of the cell to output image data	A MOS-based active pixel sensor cell utilizes the parasitic bipolar action of the cell to produce a horizontal current in lieu of the vertical image current associated with conventional bipolar-based active pixel sensor cells. Image data is collected during an integration period by applying a negative voltage to the gate of the MOS transistor which is sufficient to reverse-bias both the source/body and drain/body junctions. Following this, the image data is read out by raising the gate voltage such that the source/body junction remains reverse-biased and the drain/body	257/291		257/290 ; 257/353 ; 257/354	Chi, Min-Hwa, et al.	☐	☒	☐	☐	☐	☐	☐	☐	☐
30	US 5867318 A		USPAT	19990202	8	Wide-angle optical system	An optical system affords wide-angle imaging with a width in azimuth and a height in elevation respectively greater than and less than those of the field of view of an imaging device to which it is fitted. A median optical axis images a central format view on the optical axis of the imaging device, and two lateral optical paths image two lateral format views on a bearing axis at a bearing angle to the optical axis equal to the width in azimuth of the field of view of the imaging device. The three paths juxtaposed in the wide-angle	359/618		359/419 ; 359/431 ; 359/504	Cordier, Chantal, et al.	☐	☒	☐	☐	☐	☐	☐	☐	☐

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31	US 5873003 A		USPAT	19990216	46	Sight line detector, display unit, view finder and unit and camera with the same display unit	There is provided a liquid crystal unit having an on-chip photodetector. On a transparent substrate are laid down a metallic wiring, an n-type a-Si, an a-SiGe, and a p-type a-Si successively, an insulating film is formed, and then a transparent electrode is formed to have a light	396/51			Inoue, Shunsuke, et al.	☐	☒	☐	☐	☐	☐	☐	☐	☐
32	US 5879447 A		USPAT	19990309	152	Semiconductor device and its fabricating method	A single crystal and a polycrystal having an excellent crystal quality and providing a highly reliable semiconductor device are formed by solid phase growth at low temperatures. An amorphous thin film is deposited on a substrate such that an average inter-atomic distance of main constituent element of the amorphous thin film is 1.02 times or more of an average inter-atomic distance of the elements in single crystal, and crystallization energy is applied to the amorphous thin film to perform solid phase growth to thereby form a single crystal. In another embodiment	117/8		117/9 ; 117/930	Okada, Takako, et al.	☐	☒	☐	☐	☐	☐	☐	☐	☐

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33	US 5903492 A		USPAT	19990511	199	Semiconductor memory device and various systems mounting them	A computer system is characterized by comprising a microprocessor for performing various arithmetic processing operations, an input/output device connected to said microprocessor to send/receive data to/from an external device; and a semiconductor memory device connected to said microprocessor to store data, wherein said semiconductor memory device includes a plurality of memory cells each having a transistor having a source terminal and a drain terminal and a ferroelectric capacitor having a first terminal connected to said source terminal and a second terminal	365/145		365/149 ; 365/207 ; 365/210	Takashima, Daisaburo	☐	☒	☐	☐	☐	☐	☐	☐	☐
34	US 5923071 A		USPAT	19990713	30	Semiconductor device having a semiconductor film of low oxygen concentration	A semiconductor substrate having a silicon-on-insulator structure may achieve superior performance by utilizing a low oxygen content monocrystalline silicon thin film layer for device formation. A supporting substrate, which may comprise a transparent material, such as quartz; or which may be silicon, has an insulating film disposed thereover. The insulating film preferably has a lower diffusion coefficient with respect to impurities than the monocrystalline silicon thin film, which is provided thereover. In accordance with this structure, oxygen particles	257/458		257/347 ; 257/438 ; 257/443 ; 257/446 ; 257/447 ; 257/448 ; 257/460 ; 257/463 ; 257/466 ; 257/914	Saito, Yutaka	☐	☒	☐	☐	☐	☐	☐	☐	☐